TOSHIBA Transistor Silicon PNP Epitaxial Type (PCT Process)

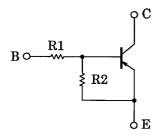
RN2107F,RN2108F,RN2109F

Switching, Inverter Circuit, Interface Circuit and Driver Circuit Applications

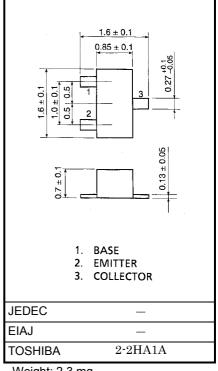
Unit in mm

- With built-in bias resistors
- Simplify circuit design
- Reduce a quantity of parts and manufacturing process
- Complementary to RN1107F~RN1109F

Equivalent Circuit and Bias Resister Values



Type No.	R1 (kΩ)	R2 (kΩ)
RN2107F	10	47
RN2108F	22	47
RN2109F	47	22



Weight: 2.3 mg

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating	Unit		
Collector-base voltage	RN2107F	V_{CBO}	-50	V	
Collector-emitter voltage	~RN2109F	V _{CEO}	-50	V	
	RN2107F		-6		
Emitter-base voltage	RN2108F	V _{EBO}	-7	V	
	RN2109F		-15		
Collector current		I _C	-100	mA	
Collector power dissipation	RN2107F	PC	100	mW	
Junction temperature	~RN2109F	Tj	150	°C	
Storage temperature range		T _{stg}	-55~150	°C	

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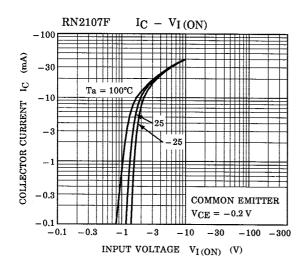
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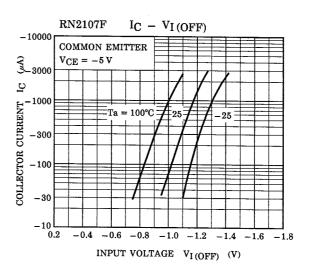
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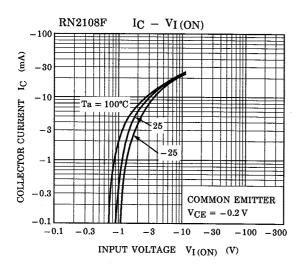
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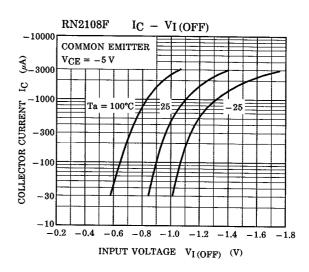
Electrical Characteristics (Ta = 25°C)

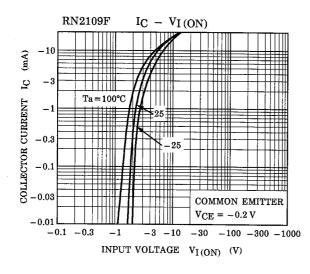
Characteri	stic	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit
	RN2107F	I _{CBO}		$V_{CB} = -50V, I_{E} = 0$	_	1	-100	nA
	~RN2109F	I _{CEO}		$V_{CE} = -50V, I_B = 0$	_	-	-500	nA
Emitter cut-off current	RN2107F	I _{EBO}	_	$V_{EB} = -6V, I_C = 0$	-0.081	_	-0.15	mA
	RN2108F			V _{EB} = -7V, I _C = 0	-0.078	_	-0.145	
	RN2109F			V _{EB} = −15V, I _C = 0	-0.167	_	-0.311	
	RN2107F	h _{FE}		V _{CE} = -5V, I _C = -10mA	80	_	_	_
DC current gain	RN2108F		_		80	_	_	
	RN2109F				70	_	_	
Collector-emitter saturation voltage	RN2107F ~RN2109F	V _{CE} (sat)	_	I _C = -5mA, I _B = -0.25mA	_	-0.1	-0.3	V
Input voltage (ON)	RN2107F	V _{I (ON)}		V _{CE} = -0.2V, I _C = -5mA	-0.7	-	-1.8	V
	RN2108F		_		-1.0	_	-2.6	
	RN2109F				-2.2	_	-5.8	
	RN2107F	V _{I (OFF)}	_	V _{CE} = -5V, I _C = -0.1mA	-0.5	_	-1.0	٧
Input voltage (OFF)	RN2108F				-0.6	_	-1.16	
	RN2109F				-1.5	_	-2.6	
Transition frequency	RN2107F ~RN2109F	f _T	_	V _{CE} = -10V, I _C = -5mA	_	200	_	MHz
Collector Output capacitance	RN2107F ~RN2109F	C _{ob}	_	$V_{CB} = -10V, I_E = 0,$ f = 1MH _z	_	3	6	pF
Input resistor	RN2107F	R1	-	_	7	10	13	kΩ
	RN2108F				15.4	22	28.6	
	RN2109F				32.9	47	61.1	
Resistor ratio	RN2107F				0.191	0.213	0.232	_
	RN2108F	R1/R2	R2 —		0.421	0.468	0.515	
	RN2109F				1.92	2.14	2.35	

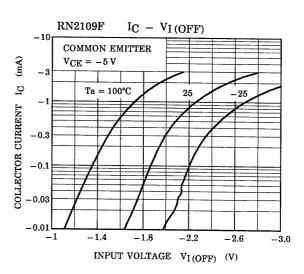


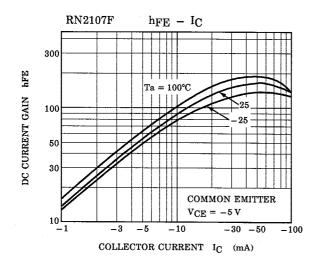


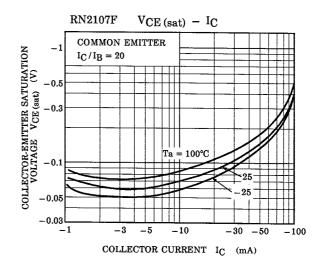


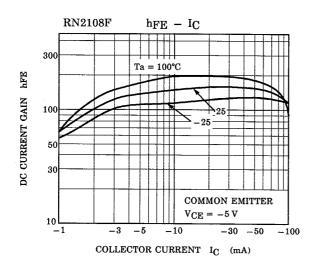


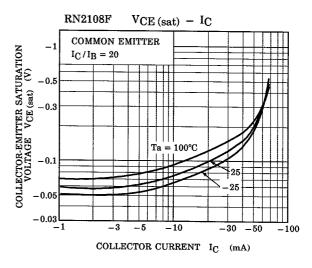


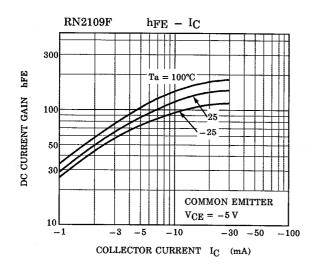


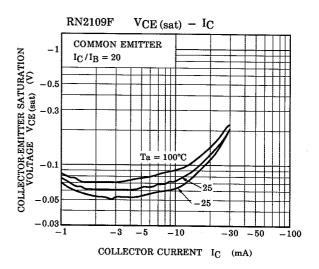












Type Name	Marking
RN2107F	Type Name Y H
RN2108F	Type Name Y I
RN2109F	Type Name Y J

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